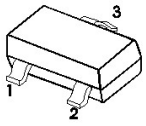
SOT-23 TRANSISTOR(PNP)



1. BASE
2. EMITTER
3. COLLECTOR

Marking:

BC856A=3A	BC856B=3B	
BC857A=3E	BC857B=3F	BC857C=3G
BC858A=3J	BC858B=3K	BC858C=3L

特征 Features

- Complementary to BC846/BC847/BC848
- Power Dissipation of 200mW
- Ideally suited for automatic insertion
- For switching and AF amplifier applications

机械数据 Mechanical Data

- Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

极限值和温度特性(TA = 25℃ 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol		数值 Value	单位 Unit
Collector-Base Voltage	V_{CBO}	BC856 BC857 BC858	-80 -50 -30	V
Collector-Emitter Voltage	V_{CEO}	BC856 BC857 BC858	-65 -45 -30	V
Emitter -Base Voltage	V_{EBO}		-6	V
Collector Current-Continuous	I_C		-100	mA
Collector Power Dissipation	P_C		200	mW
Junction Temperature	T_j		150	℃
Storage Temperature	Tstg		-55-+150	℃
Thermal resistance From junction to ambient	$R_{\theta JA}$		625	℃/W

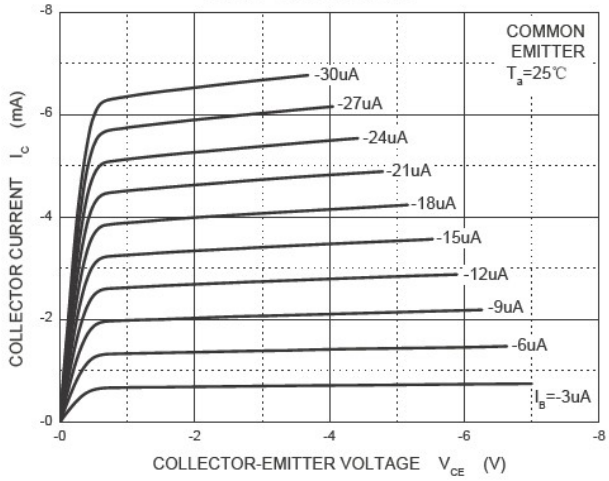
电特性 (TA = 25℃ 除非另有规定)

Electrical Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified).

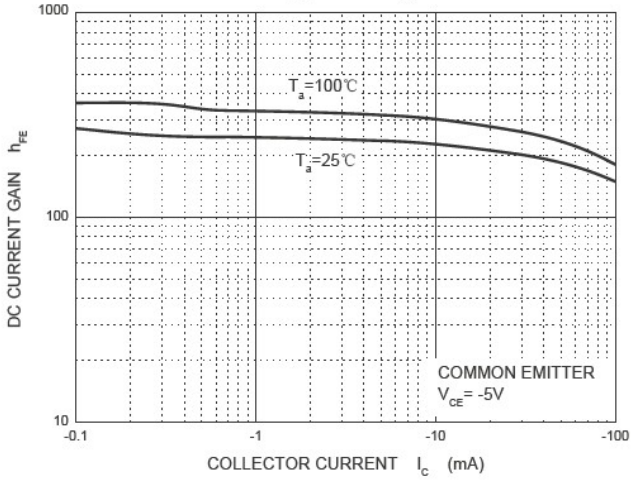
参数 Parameter	符号 Symbols	测试条件 Test Condition		界限 Limits Min	 Max	单位 Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10uA, I_E=0	BC856 BC857 BC858	-80 -50 -30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	BC856 BC857 BC858	-65 -45 -30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10uA, I_C=0		-6		V
Collector cut-off current	I_{CBO}	V_{CB}=-70V, I_E=0 V_{CB}=-45V, I_E=0 V_{CB}=-25V, I_E=0	BC856 BC857 BC858		-100	nA
Collector cut-off current	I_{CEO}	V_{CE}=-60V, I_B=0 V_{CE}=-40V, I_B=0 V_{CE}=-25V, I_B=0	BC856 BC857 BC858		-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-2mA	BC856A;BC857A;BC858A BC856B;BC857B;BC858B BC857C;BC858C	125 220 420	250 475 800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-5mA			-0.50	V
Base -emitter saturation voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-5mA			-1.10	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA,f=100MHz		100		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, f=1MHz			4.5	pF

Typical characteristics

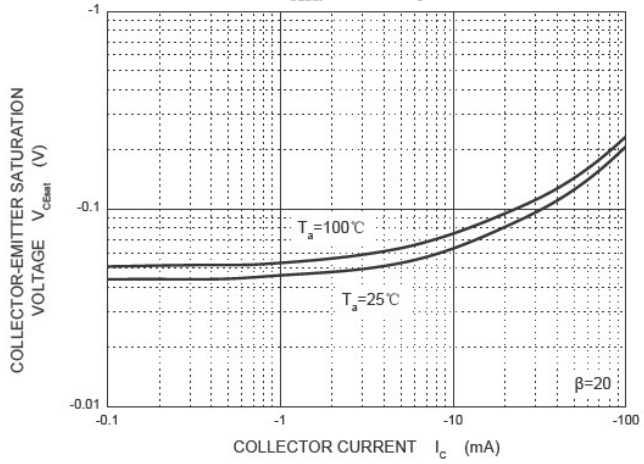
Static Characteristic



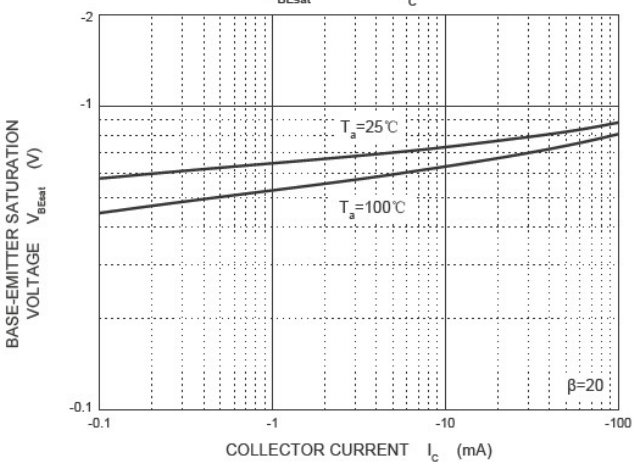
h_{FE} —— I_C



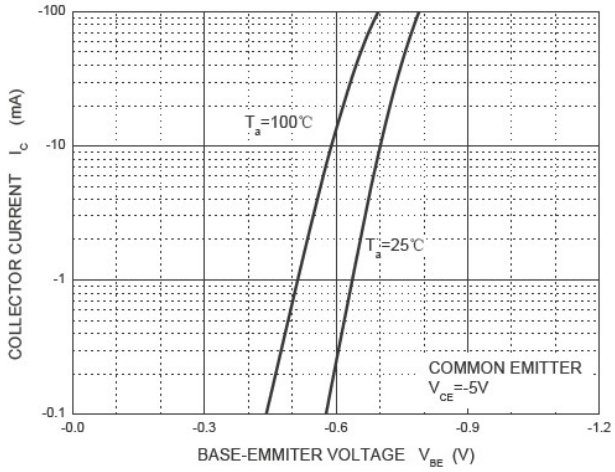
V_{CEsat} —— I_C



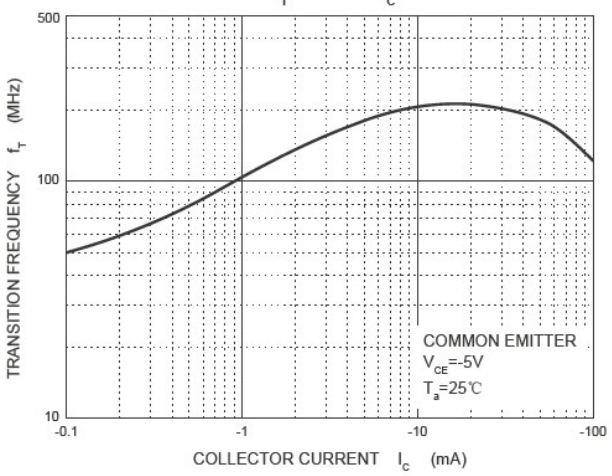
V_{BEsat} —— I_C

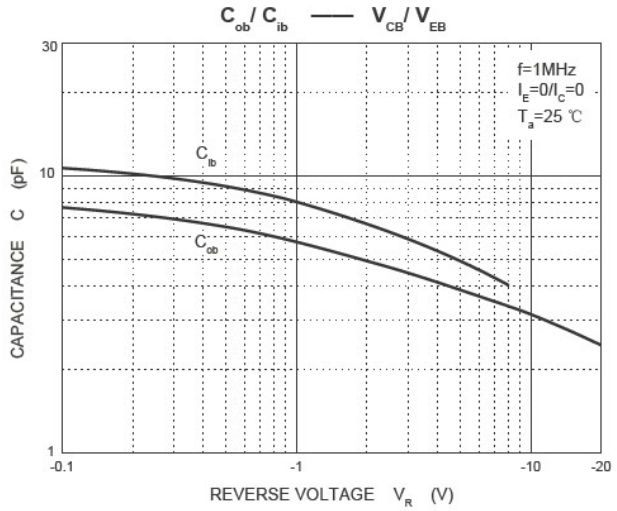


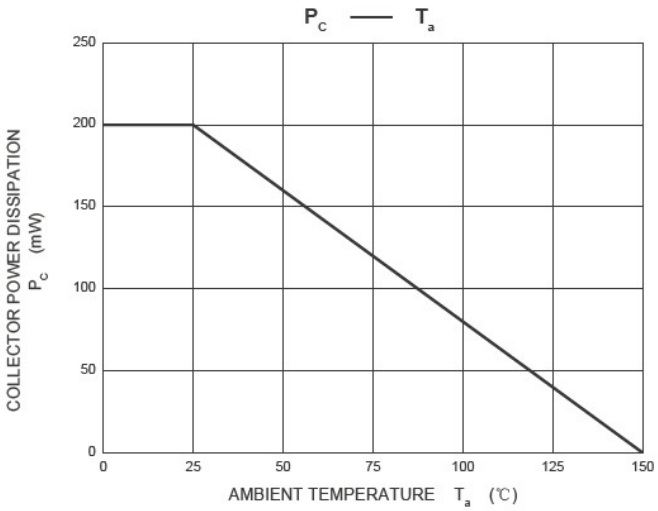
I_C —— V_{BE}



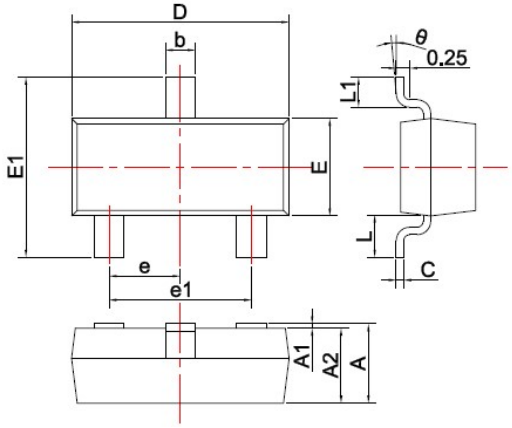
f_T —— I_C







SOT-23 PACKAGE OUTLINE Plastic surface mounted package

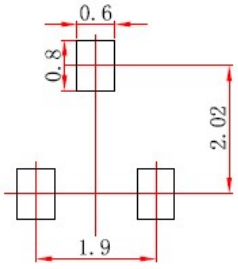


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Unit: mm

焊盘设计参考Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



Note:
1.Controlling dimension:In millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.